

Z-Contrast Electron Tomography of Embedded Nanocrystals

Ute Kaiser¹, Andrey Chuvilin¹ and Christian Kübel²

¹Universität Ulm, Materialwissenschaftliche Elektronenmikroskopie, Albert Einstein Allee 11, 89069, Germany ²Fraunhofer Institut IFAM, Adhesive Bonding Technology and Surfaces, Wiener Straße 12, 28359 Bremen, Germany

OUTLINE

Applications based on well organised nanocrystals embedded in crystalline matrices are the target in different new fields of nanoscience (e.g. [1]). The nanocrystals have to be characterized close to the atomic level to understand and modify their:

- formation process
- small-size properties, size and shape dependent properties [1, 2].
- To calculate properties of new nanoobjects correctly, 3D-information on size and shape is essential [2].

As precipitates usually differ from the matrix by elemental content, Z-contrast tomography is well suited. Thanks to the principle of reciprocity, Z-contrast tomography already successfully realized in a STEM (HAADF-STEM-Tomography [3], [4]) should be obtainable in a conventional TEM, and should give, in principle, the same resolution. As conventional TEMs are still wider spread than FEG-TEM/STEM machines, a Z-contrast tomography technique applicable in a conventional TEM is very desirable.

Here we report on:

the test and application of High Angle Centered Dark Field (HACDF) [5] Electron Tomography and on the comparison to HAADF-STEM-Tomography. As example we use ErSi2 nanocrystals embedded in SiC. (For application to catalyst please see our poster MS2#19)

 the new insight into the nanocrystal formation process of ErSi2 nanocrystals embedded in SiC obtained from electron tomography and 3D-reconstruction compared to 2D-imaging [6, 7].

- E. L. Wolf, Naxophysics and Naxotschwology: An Tatroduction to Modern Concepts in Naxoscience Wiley-Vch 2004
 Bechstrach, F., Frissal, A., Furthmiller, J. V., Kaiser, H.-Ch. Weissker, W. Wesch, Quantum structures in Sic, Appl.
 Surf. Science 2222-223 (2003) 302-495 (2004) 414
 C. Kaiser, A. Midgley, M. Weyland, 3D electron microscopy in the physical sciences: the development of Z-contrast and
 ETFEX transgraphy. Ultramaicroscopy 69 (2003) 413-431
 C. Kikel et al., Microscopy and Microarophysis. 2005, 11(5), in print
 U. Kaiser, A. Chwilin, Enhanced competitional contrast in imaging of nanoprecipitates buried in a defective crystal
 using a conventional TEM, Microscopy and Microarophysis. (2003), 10(3), 36-41
 U. Kaiser, A. Muller, J.L. Grazul, A. Chwilin, M. Kawasaki, From atems to embedded nanocrystals: Direct
 abservation of defect mediated cluster formation, Nature Materials, I (2002) 102-105
 T. U. Kaiser, J. Sakugaki, K. Gerture, Faulted GeSi and Si nanocrystals buried in hexagonal SiC
 Phil. Mag. Lett. (2003) 83, 4, 253-263

HACDF-Method

 \mapsto IFAM



Within the centred objective aperture thermal diffuse scattered electron are collected at the optical axis of the TEM (imaging conditions are the same as for HRTEM) [5].

HACDF-TEM Tomography visualised in 3D.

Comparison of HACDF-TEM and HAADF-STEM Tomography

xample: ErSl, nanocrystals embedded in 4H-SiC created after high dose and high temperature Er ion implantation and high temperature annealing Ch. Schubert, U. Kaiser, A. Hedler, W. Wesch, T. Gorelik, U. Glatzel, J. Krudilich, B. Wunderlich, G. Heß, K. Goetz, Nanocrystal formation in SiC by Ge ion implantation and subsequent thermal annealing, Journal of Applied Physics 91/3 (2002) 1520-1524



Z-Contrast Electron Tomography: New insight into the nanocrystal formation process.

As can be seen: Reconstructed nanocrystals obtained by Z-Contrast TEM and -STEM Electron Tomography give about the same result. The methods do not differ significantly in resolution.

hill-like shape of the ErSi2 nanocrystals.

revealed.

foreign atoms





Optical photograph of a bulk SiC crystal



The nanocrystals are well facetted in 11-20 projection (not hill-like shaped!!)
 In 0001 projection the nanocrystal show very pronounced facets. These facets are those of the basal 0001 SiC

Two crystals, reconstructed from



plane (see the SiC crystal). We conclude that it is the SiC matrix which determines the facets of the NC. 3. Bright stripes could be imaged, which originate from cores of dislocations containing Er atoms. These stripes are connected to the nanocrystals, indicating that dislocation cores serve as preferable diffusion paths for

F



What we knew from 2D-HAADF-STEM inspection of the sample (see the left row of figures) 1. ErSi2 nanocrystals are of hill-like shape; no relationship between nanocrystal faces and matrix faces were

2. The chemical reaction between Er (foreign atoms) and Si (of the matrix) was suggested to be the origin of the

3. ErSi2 NCs form from a single foreign atom column, nucleated at a matrix defect (interstitial loop) over a state of 2D-Er-defects. However, the role of the interstitial loops in the diffusion mechanism is not clear so far.

U. Kaiser, D. A. Muller, J. L. Grazul, A. Chuvilin and M. Kawasaki: From atoms to embedded nanocrystals: Direct observation of defect mediated cluster formation Nature Materials, 1 (2002) 102-105